GP1S58VJ000F

Gap : 5mm, Slit : 0.5mm
Phototransistor Output,
Case package Transmissive
Photointerrupter

■ Description

GP1S58VJ000F is a standard, phototransistor output, transmissive photointerrupter with opposing emitter and detector in a case, providing non-contact sensing. For this family of devices, the emitter and detector are inserted in a case, resulting in a through-hole design.

This device uses positioning pins to insure accurate placement and avoid miss-orientation of the emitter and detector.

■ Features

1. Transmissive with phototransistor output
2. Highlights :
   - Vertical Slit for alternate motion detection
   - Positioning Pin to prevent misalignment
3. Key Parameters :
   - Gap Width : 5mm
   - Slit Width (detector side): 0.5mm
   - Package : 13.7×10×5.2mm
4. Lead free and RoHS directive compliant

■ Agency approvals/Compliance

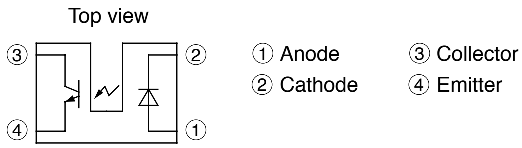
1. Compliant with RoHS directive

■ Applications

1. General purpose detection of object presence or motion.
2. Example : Printer, FAX, Optical storage unit

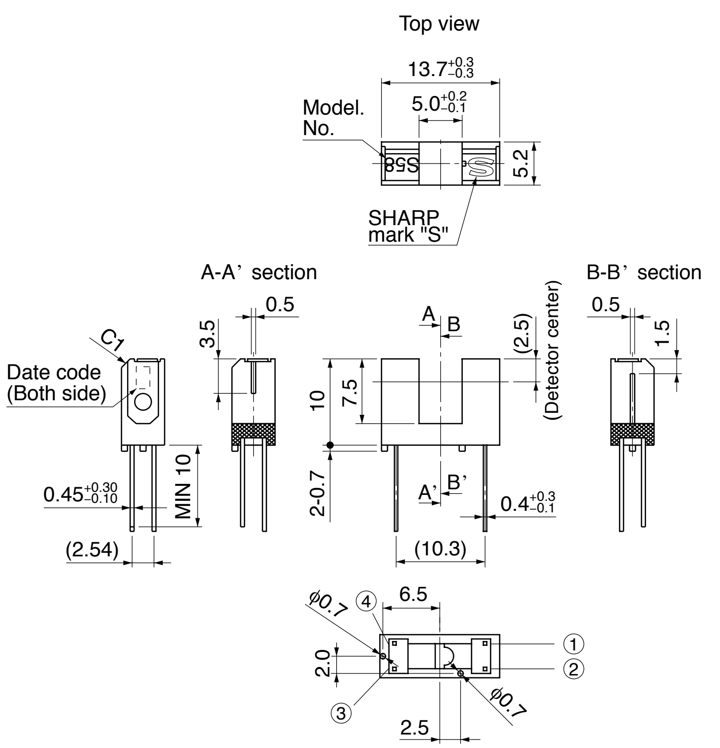
Sheet No.: D3-A02702EN
Date Sep. 1. 2006

■ Internal Connection Diagram



■ Outline Dimensions

(Unit : mm)



• Unspecified tolerance shall be as follows ;

Dimensions (d)	Tolerance
d≤6.0	±0.1
6.0<d≤18.0	±0.2

• ( ) : Reference dimensions

Product mass : approx. 0.5g

Dip soldering material : Sn−3Ag−0.5Cu

Date code (2 digit)

1st digit		2nd digit	
Year of production		Month of production	
A.D.	Mark	Month	Mark
2000	0	1	1
2001	1	2	2
2002	2	3	3
2003	3	4	4
2004	4	5	5
2005	5	6	6
2006	6	7	7
2007	7	8	8
2008	8	9	9
2009	9	10	X
2010	0	11	Y
:	:	12	Z

repeats in a 10 year cycle

Country of origin

Japan, Indonesia or Philippines
(Indicated on the packing case)

■ Absolute Maximum Ratings

(T_a=25˚C)

Parameter		Symbol	Rating	Unit
Input	*1 Forward current	I_F	50	mA
	*1, 2 Peak forward current	I_{FM}	1	A
	Reverse voltage	V_R	6	V
	Power dissipation	P	75	mW
Output	Collector-emitter voltage	V_{CEO}	35	V
	Emitter-collector voltage	V_{ECO}	6	V
	Collector current	I_C	20	mA
	*1 Collector power dissipation	P_C	75	mW
Operating temperature		T_{opr}	−25 to +85	˚C
Storage temperature		T_{stg}	−40 to +100	˚C
*3 Soldering temperature		T_{sol}	260	˚C

*1 Refer to Fig. 1, 2, 3
*2 Pulse width ≤ 100μs, Duty ratio=0.01
*3 For 5s or less

■ Electro-optical Characteristics

(T_a=25˚C)

Parameter			Symbol	Condition	MIN.	TYP.	MAX.	Unit
Input	Forward voltage		V_F	I_F=20mA	–	1.25	1.4	V
	Peak forward voltage		V_{FM}	I_{FM}=0.5A		3	4	V
	Reverse current		I_R	V_R=3V	–	–	10	μA
Output	Collector dark current		I_{CEO}	V_{CE}=20V	–	1	100	nA
Transfer charac-teristics	Collector current		I_C	V_{CE}=5V, I_F=20mA	0.5	–	15	mA
	Collector-emitter saturation voltage		$V_{CE(sat)}$	I_F=40mA, I_C=0.2mA	–	–	0.4	V
	Response time	Rise time	t_r	V_{CE}=2V, I_C=2mA, R_L=100Ω	–	3	15	μs
		Fall time	t_f		–	4	20	

Fig.1 Forward Current vs. Ambient Temperature

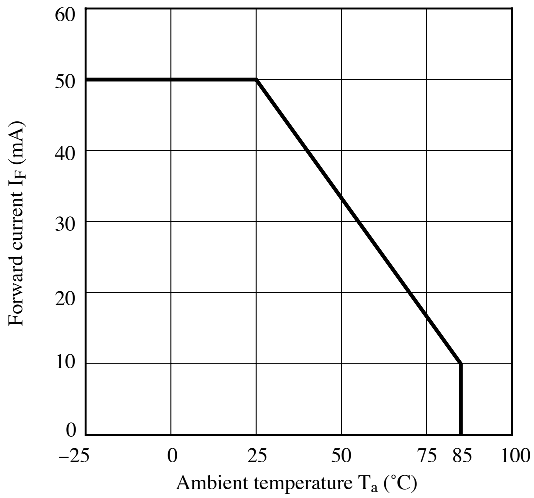


Fig.2 Collector Power Dissipation vs. Ambient Temperature

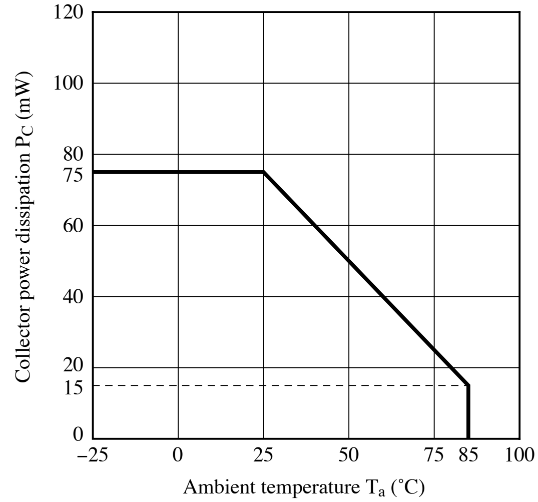


Fig.3 Peak Forward Current vs. Duty Ratio

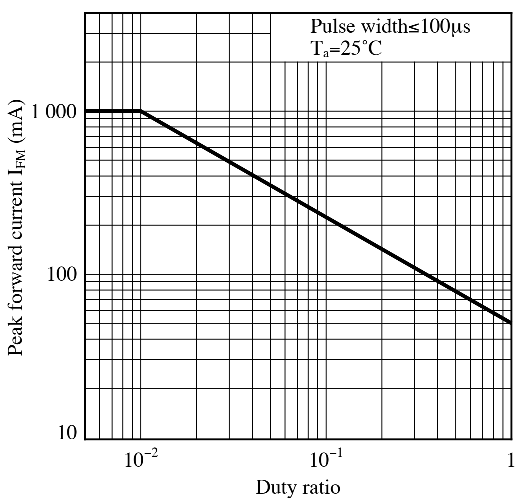


Fig.4 Forward Current vs. Forward Voltage

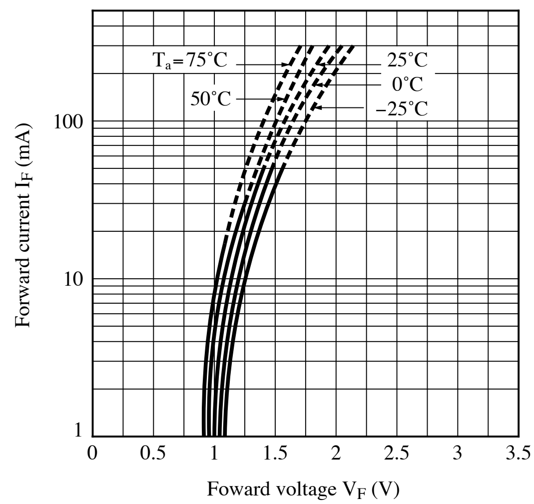


Fig.5 Collector Current vs. Forward Current

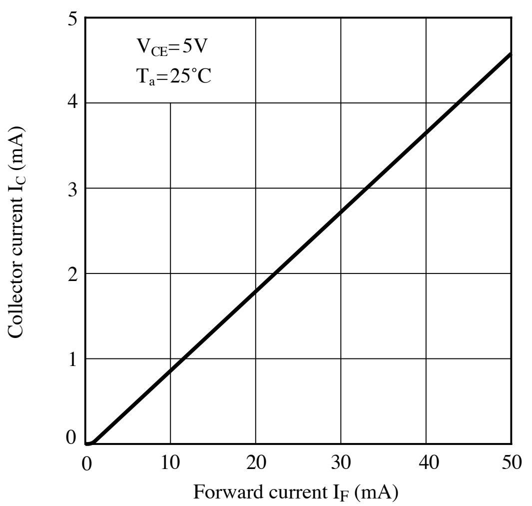


Fig.6 Collector Current vs. Collector-emitter Voltage

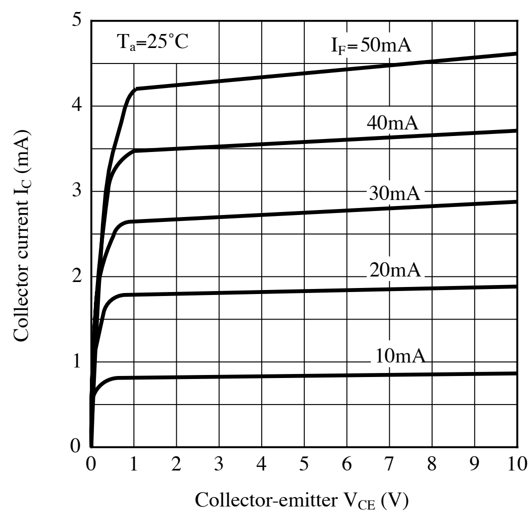


Fig.7 Collector Current vs. Ambient Temperature

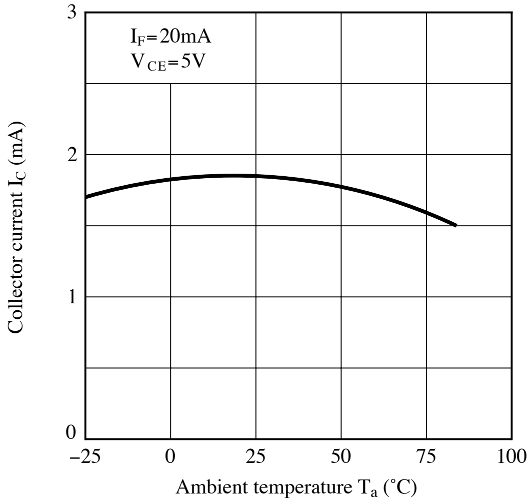


Fig.8 Collector-emitter Saturation Voltage vs. Ambient Temperature

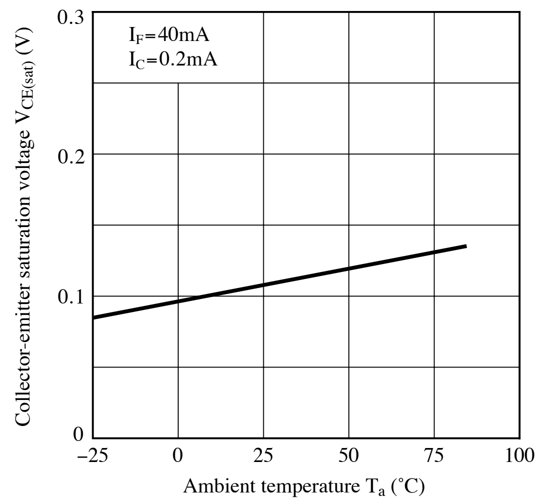


Fig.9 Response Time vs. Load Resistance

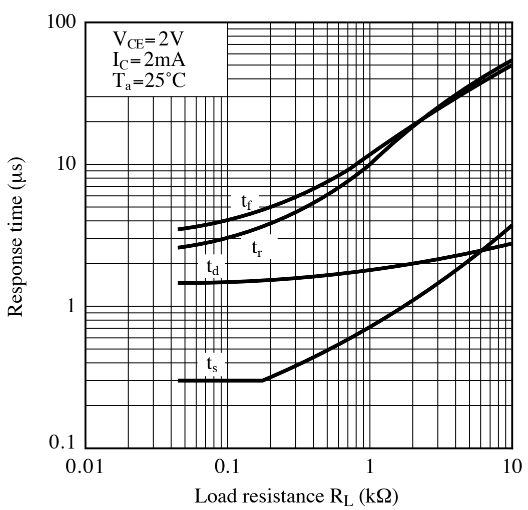


Fig.10 Test Circuit for Response Time

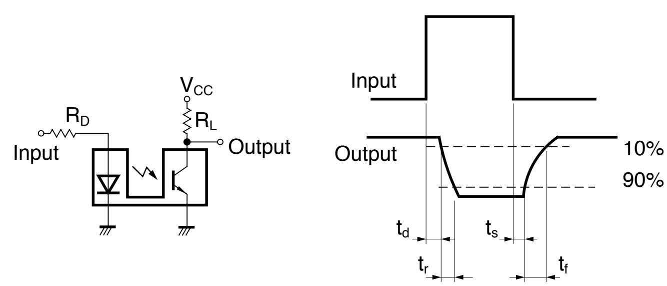


Fig.11 Frequency Response

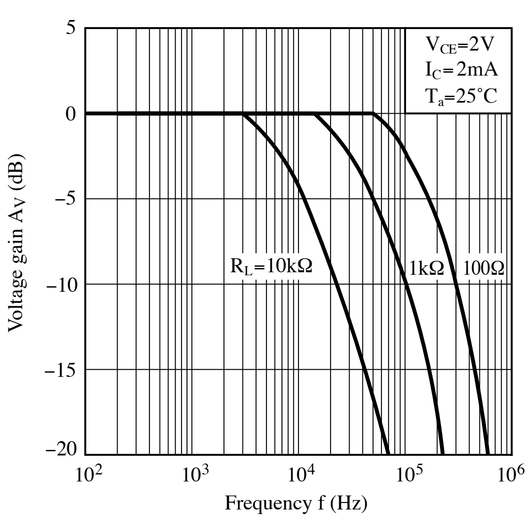


Fig.12 Collector Dark Current vs. Ambient Temperature

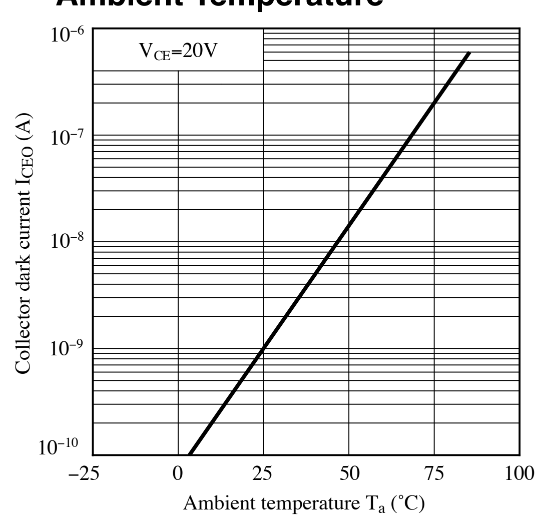


Fig.13 Detecting Position Characteristics (1)

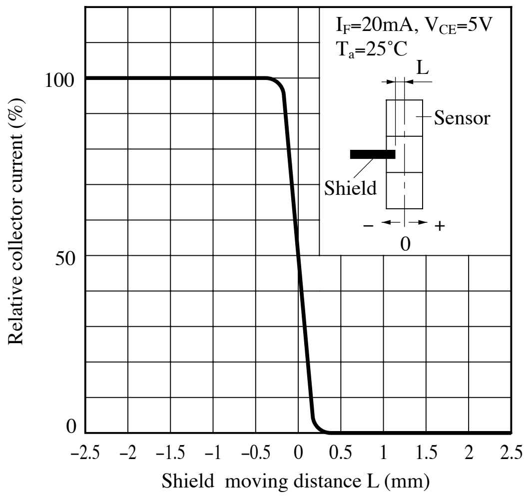
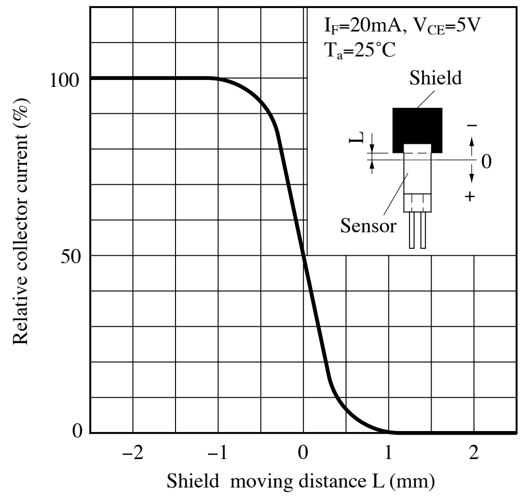


Fig.14 Detecting Position Characteristics (2)



Remarks : Please be aware that all data in the graph are just for reference and not for guarantee.

■Design Considerations

● Design guide

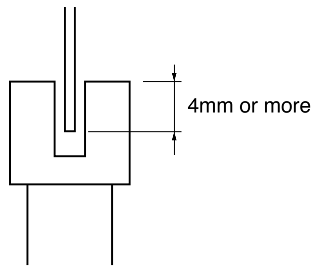
1) Prevention of detection error

To prevent photointerrupter from faulty operation caused by external light, do not set the detecting face to the external light.

2) Position of opaque board

Opaque board shall be installed at place 4mm or more from the top of elements.

(Example)



This product is not designed against irradiation and incorporates non-coherent IRED.

● Degradation

In general, the emission of the IRED used in photocouplers will degrade over time.

In the case of long term operation, please take the general IRED degradation (50% degradation over 5 years) into the design consideration.

● Parts

This product is assembled using the below parts.

• Photodetector (qty. : 1)

Category	Material	Maximum Sensitivity wavelength (nm)	Sensitivity wavelength (nm)	Response time (μs)
Phototransistor	Silicon (Si)	800	400 to 1 200	3

• Photo emitter (qty. : 1)

Category	Material	Maximum light emitting wavelength (nm)	I/O Frequency (MHz)
Infrared emitting diode (non-coherent)	Gallium arsenide (GaAs)	950	0.3

• Material

Case	Lead frame plating
Black NORYL resin	Solder dip. (Sn–3Ag–0.5Cu)

■ Manufacturing Guidelines

● Soldering Method

Flow Soldering:

Soldering should be completed below 260˚C and within 5 s.
Please take care not to let any external force exert on lead pins.
Please don't do soldering with preheating, and please don't do soldering by reflow.

Hand soldering

Hand soldering should be completed within 3 s when the point of solder iron is below 350˚C.
Please solder within one time.
Please don't touch the terminals directly by soldering iron.
Soldered product shall treat at normal temperature.

Other notice

Please test the soldering method in actual condition and make sure the soldering works fine, since the impact on the junction between the device and PCB varies depending on the cooling and soldering conditions.

Flux

Some flux, which is used in soldering, may crack the package due to synergistic effect of alcohol in flux and the rise in temperature by heat in soldering. Therefore, in using flux, please make sure that it does not have any influence on appearance and reliability of the photointerrupter.

● Cleaning instructions

Solvent cleaning :

Solvent temperature should be 45˚C or below. Immersion time should be 3 minutes or less.

Ultrasonic cleaning :

The affect to device by ultrasonic cleaning is different by cleaning bath size, ultrasonic power output, cleaning time, PCB size or device mounting condition etc.

Please test it in actual using condition and confirm that doesn't occur any defect before starting the ultrasonic cleaning.

Recommended solvent materials :

Ethyl alcohol, Methyl alcohol and Isopropyl alcohol.

● Presence of ODC

This product shall not contain the following materials.
And they are not used in the production process for this product.
Regulation substances : CFCs, Halon, Carbon tetrachloride, 1.1.1-Trichloroethane (Methylchloroform)

Specific brominated flame retardants such as the PBB and PBDE are not used in this product at all.

This product shall not contain the following materials banned in the RoHS Directive (2002/95/EC).

- •Lead, Mercury, Cadmium, Hexavalent chromium, Polybrominated biphenyls (PBB), Polybrominated diphenyl ethers (PBDE).

■ Package specification

● Case package

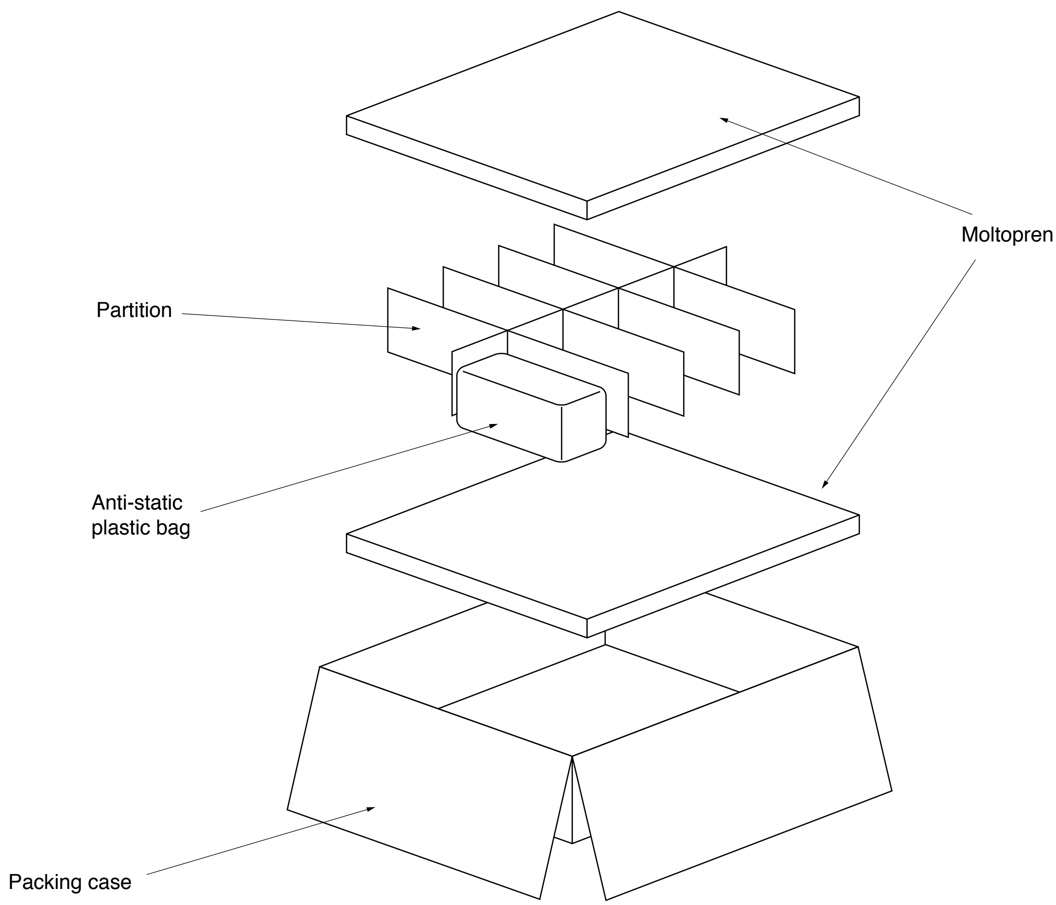
Package materials

Anti-static plastic bag : Polyethtylene
Moltopren : Urethane
Partition : Corrugated fiberboard
Packing case : Corrugated fiberboard

Package method

100 pcs of products shall be packaged in a plastic bag, Ends shall be fixed be by stoppers. The bottom ot the packing case is covered with moltopren, and the partition is set in the packing case. Each partition should have 1 plastic bag.
The 10 plastic bags containing a product are put in the packing case.
Moltopren should be located after all product are settled (1 packing contains 1 000 pcs).

Packing composition



■ Important Notices

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(i) The devices in this publication are designed for use in general electronic equipment designs such as:

--- Personal computers
--- Office automation equipment
--- Telecommunication equipment [terminal]
--- Test and measurement equipment
--- Industrial control
--- Audio visual equipment
--- Consumer electronics

(ii) Measures such as fail-safe function and redundant design should be taken to ensure reliability and safety when SHARP devices are used for or in connection with equipment that requires higher reliability such as:

--- Transportation control and safety equipment (i.e., aircraft, trains, automobiles, etc.)
--- Traffic signals
--- Gas leakage sensor breakers
--- Alarm equipment
--- Various safety devices, etc.

(iii) SHARP devices shall not be used for or in connection with equipment that requires an extremely high level of reliability and safety such as:

--- Space applications
--- Telecommunication equipment [trunk lines]
--- Nuclear power control equipment
--- Medical and other life support equipment (e.g., scuba).

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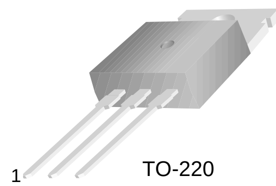
FAIRCHILD SEMICONDUCTOR®

TIP120/121/122

Medium Power Linear Switching Applications

- Complementary to TIP125/126/127



TO-220

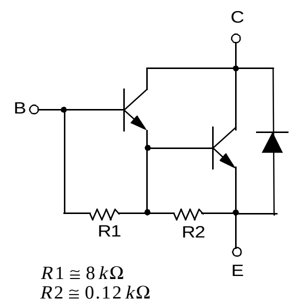
1.Base 2.Collector 3.Emitter

NPN Epitaxial Darlington Transistor

Absolute Maximum Ratings T_C=25°C unless otherwise noted

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage : TIP120 : TIP121 : TIP122	60 80 100	V V V
V_{CEO}	Collector-Emitter Voltage : TIP120 : TIP121 : TIP122	60 80 100	V V V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current (DC)	5	A
I_{CP}	Collector Current (Pulse)	8	A
I_B	Base Current (DC)	120	mA
P_C	Collector Dissipation (T_a=25°C)	2	W
	Collector Dissipation (T_C=25°C)	65	W
T_J	Junction Temperature	150	°C
T_{STG}	Storage Temperature	- 65 ~ 150	°C

Equivalent Circuit



Electrical Characteristics T_C=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Units
V_{CEO}(sus)	Collector-Emitter Sustaining Voltage : TIP120 : TIP121 : TIP122	I_C = 100mA, I_B = 0	60 80 100		V V V
I_{CEO}	Collector Cut-off Current : TIP120 : TIP121 : TIP122	V_{CE} = 30V, I_B = 0 V_{CE} = 40V, I_B = 0 V_{CE} = 50V, I_B = 0		0.5 0.5 0.5	mA mA mA
I_{CBO}	Collector Cut-off Current : TIP120 : TIP121 : TIP122	V_{CB} = 60V, I_E = 0 V_{CB} = 80V, I_E = 0 V_{CB} = 100V, I_E = 0		0.2 0.2 0.2	mA mA mA
I_{EBO}	Emitter Cut-off Current	V_{BE} = 5V, I_C = 0		2	mA
h_{FE}	* DC Current Gain	V_{CE} = 3V,I_C = 0.5A V_{CE} = 3V, I_C = 3A	1000 1000		
V_{CE}(sat)	* Collector-Emitter Saturation Voltage	I_C = 3A, I_B = 12mA I_C = 5A, I_B = 20mA		2.0 4.0	V V
V_{BE}(on)	* Base-Emitter ON Voltage	V_{CE} = 3V, I_C = 3A		2.5	V
C_{ob}	Output Capacitance	V_{CB} = 10V, I_E = 0, f = 0.1MHz		200	pF

* Pulse Test : PW≤300µs, Duty cycle ≤2%

Typical characteristics

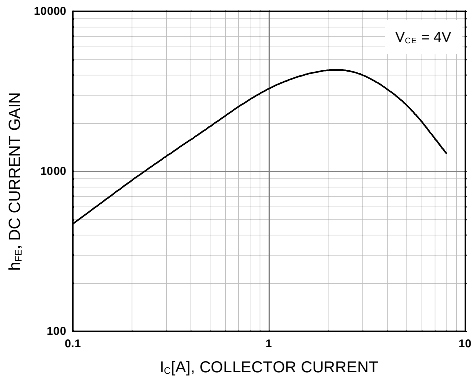


Figure 1. DC current Gain

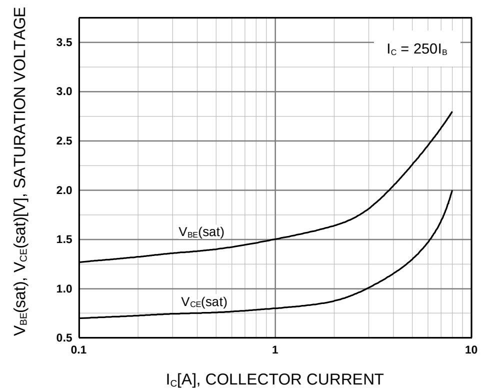


Figure 2. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

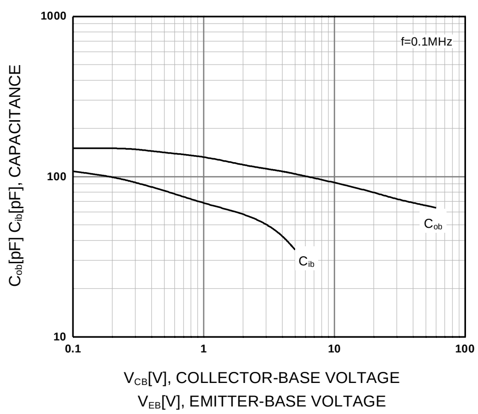


Figure 3. Output and Input Capacitance vs. Reverse Voltage

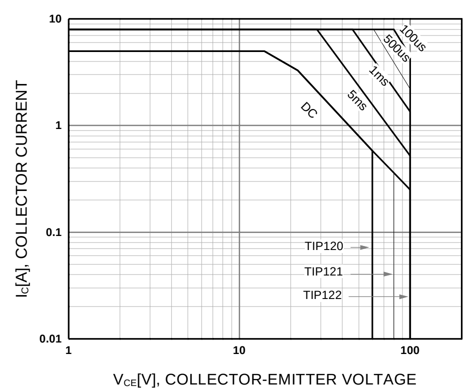


Figure 4. Safe Operating Area

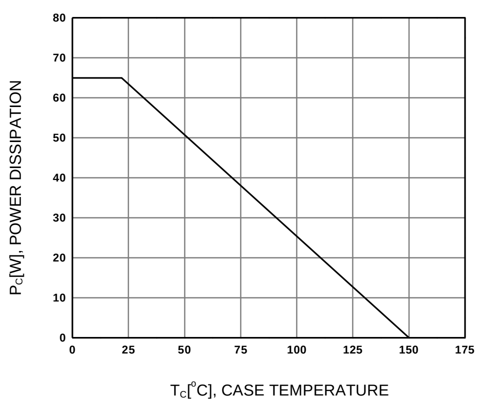
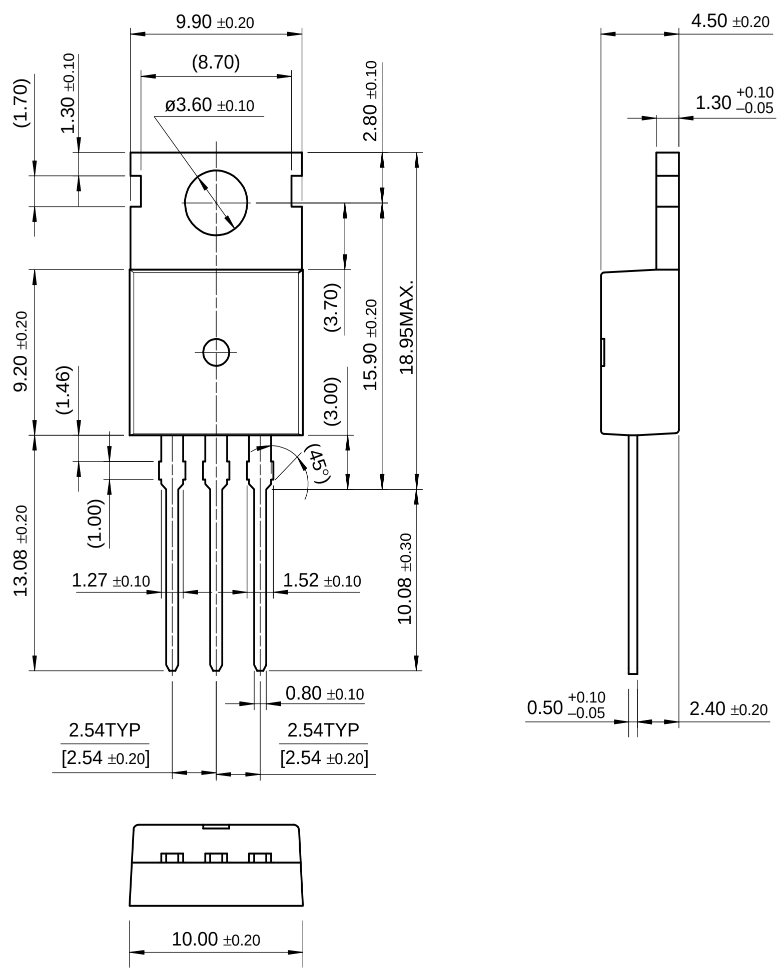


Figure 5. Power Derating

Package Demensions

TO-220



Dimensions in Millimeters

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DenseTrench™	GTO™	PowerTrench®	SuperSOT™-8
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E^2CMOS™	LittleFET™	QT Optoelectronics™	TinyLogic™
EnSigna™	MicroFET™	Quiet Series™	UHC™
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2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

PRODUCT STATUS DEFINITIONS

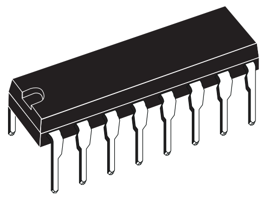
Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.

ULN2001A-ULN2002A
ULN2003A-ULN2004A

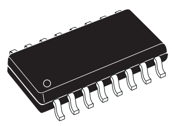
SEVEN DARLINGTON ARRAYS

- SEVEN DARLINGTONS PER PACKAGE
- OUTPUT CURRENT 500mA PER DRIVER (600mA PEAK)
- OUTPUT VOLTAGE 50V
- INTEGRATED SUPPRESSION DIODES FOR INDUCTIVE LOADS
- OUTPUTS CAN BE PARALLELED FOR HIGHER CURRENT
- TTL/CMOS/PMOS/DTL COMPATIBLE INPUTS
- INPUTS PINNED OPPOSITE OUTPUTS TO SIMPLIFY LAYOUT



DIP16

ORDERING NUMBERS: ULN2001A/2A/3A/4A



SO16

ORDERING NUMBERS: ULN2001D/2D/3D/4D

DESCRIPTION

The ULN2001A, ULN2002A, ULN2003 and ULN2004A are high voltage, high current darlington arrays each containing seven open collector darlington pairs with common emitters. Each channel rated at 500mA and can withstand peak currents of 600mA. Suppression diodes are included for inductive load driving and the inputs are pinned opposite the outputs to simplify board layout.

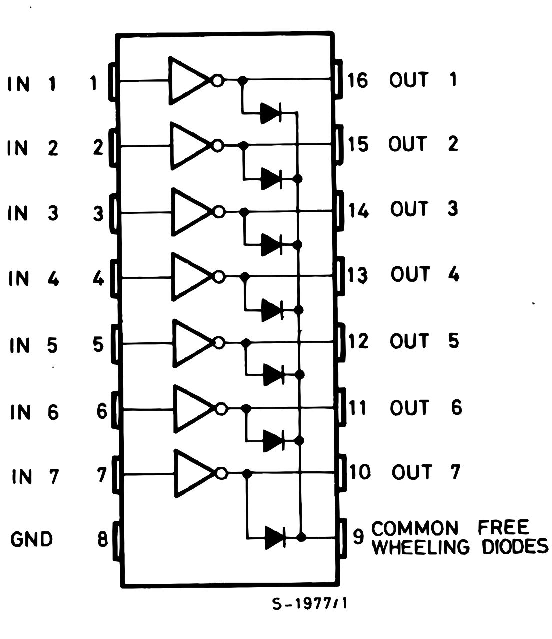
The four versions interface to all common logic families :

ULN2001A	General Purpose, DTL, TTL, PMOS, CMOS
ULN2002A	14-25V PMOS
ULN2003A	5V TTL, CMOS
ULN2004A	6–15V CMOS, PMOS

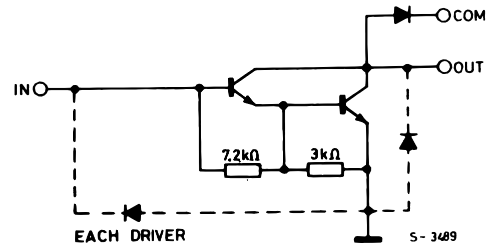
These versatile devices are useful for driving a wide range of loads including solenoids, relays DC motors, LED displays filament lamps, thermal printheads and high power buffers.

The ULN2001A/2002A/2003A and 2004A are supplied in 16 pin plastic DIP packages with a copper leadframe to reduce thermal resistance. They are available also in small outline package (SO-16) as ULN2001D/2002D/2003D/2004D.

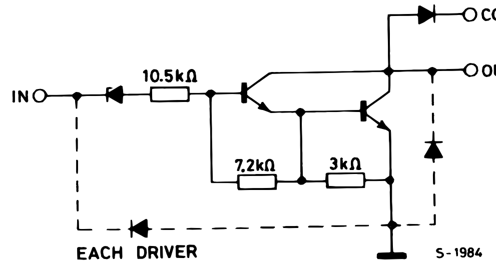
PIN CONNECTION



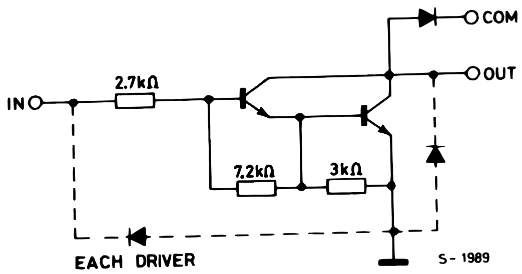
SCHEMATIC DIAGRAM



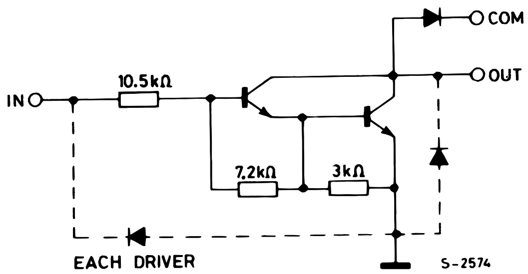
Series ULN-2001A
(each driver)



Series ULN-2002A
(each driver)



Series ULN-2003A
(each driver)



Series ULN-2004A
(each driver)

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_o	Output Voltage	50	V
V_{in}	Input Voltage (for ULN2002A/D - 2003A/D - 2004A/D)	30	V
I_c	Continuous Collector Current	500	mA
I_b	Continuous Base Current	25	mA
T_{amb}	Operating Ambient Temperature Range	– 20 to 85	°C
T_{stg}	Storage Temperature Range	– 55 to 150	°C
T_j	Junction Temperature	150	°C

THERMAL DATA

Symbol	Parameter	DIP16	SO16	Unit
$R_{th\ j\text{-}amb}$	Thermal Resistance Junction-ambient Max.	70	120	°C/W

ELECTRICAL CHARACTERISTICS (T_{amb} = 25°C unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit	Fig.
I_{CEX}	Output Leakage Current	V_{CE} = 50V T_{amb} = 70°C, V_{CE} = 50V T_{amb} = 70°C for ULN2002A V_{CE} = 50V, V_i = 6V for ULN2004A V_{CE} = 50V, V_i = 1V			50 100 500 500	µA µA µA µA	1a 1a 1b 1b
$V_{CE(sat)}$	Collector-emitter Saturation Voltage	I_C = 100mA, I_B = 250µA I_C = 200 mA, I_B = 350µA I_C = 350mA, I_B = 500µA		0.9 1.1 1.3	1.1 1.3 1.6	V V V	2 2 2
$I_{i(on)}$	Input Current	for ULN2002A, V_i = 17V for ULN2003A, V_i = 3.85V for ULN2004A, V_i = 5V V_i = 12V		0.82 0.93 0.35 1	1.25 1.35 0.5 1.45	mA mA mA mA	3 3 3 3
$I_{i(off)}$	Input Current	T_{amb} = 70°C, I_C = 500µA	50	65		µA	4
$V_{i(on)}$	Input Voltage	V_{CE} = 2V for ULN2002A I_C = 300mA for ULN2003A I_C = 200mA I_C = 250mA I_C = 300mA for ULN2004A I_C = 125mA I_C = 200mA I_C = 275mA I_C = 350mA			 13 2.4 2.7 3 5 6 7 8	V	5
h_{FE}	DC Forward Current Gain	for ULN2001A V_{CE} = 2V, I_C = 350mA	1000				2
C_i	Input Capacitance			15	25	pF	
t_{PLH}	Turn-on Delay Time	0.5 V_i to 0.5 V_o		0.25	1	µs	
t_{PHL}	Turn-off Delay Time	0.5 V_i to 0.5 V_o		0.25	1	µs	
I_R	Clamp Diode Leakage Current	V_R = 50V T_{amb} = 70°C, V_R = 50V			50 100	µA µA	6 6
V_F	Clamp Diode Forward Voltage	I_F = 350mA		1.7	2	V	7

TEST CIRCUITS

Figure 1a.

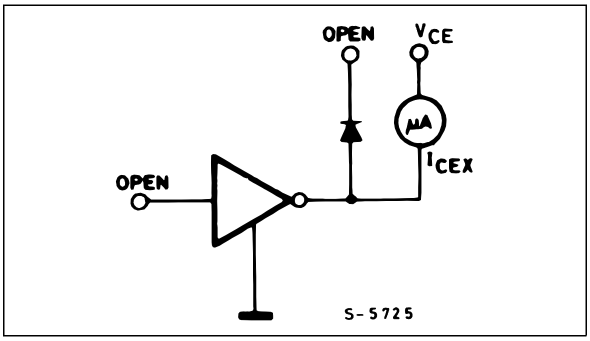


Figure 1b.

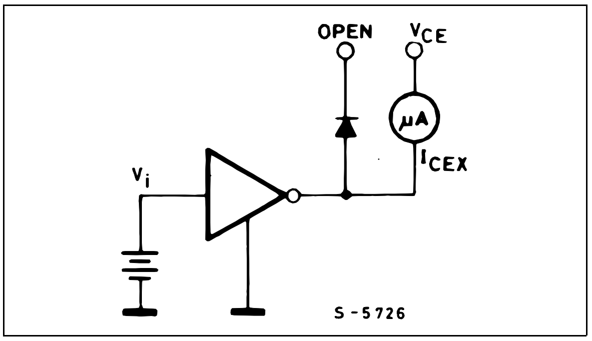


Figure 2.

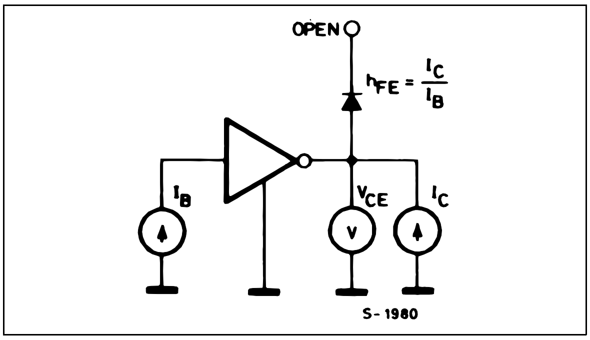


Figure 3.

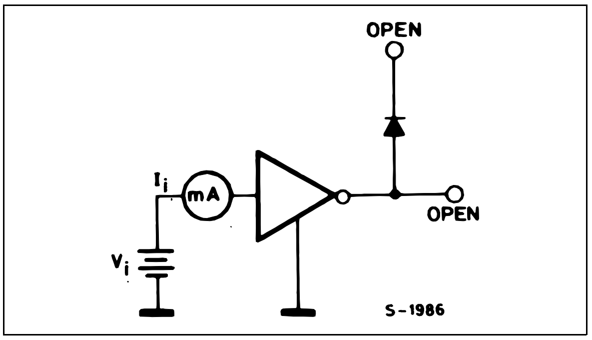


Figure 4.

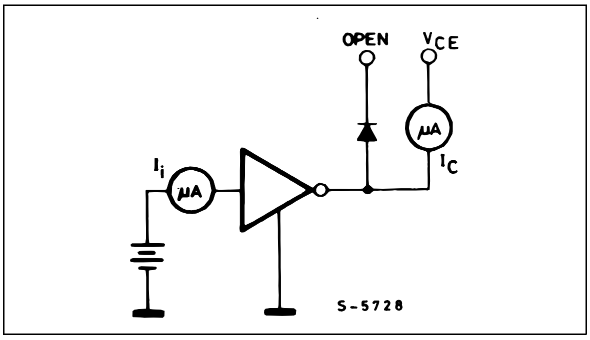


Figure 5.

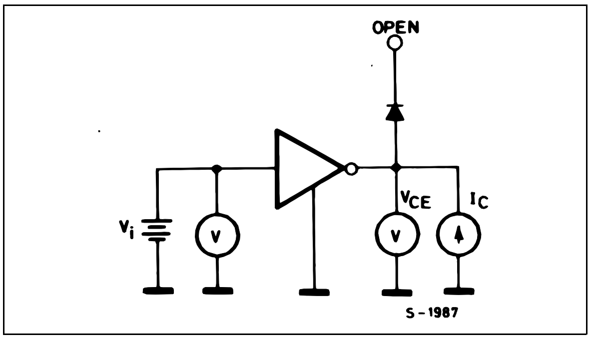


Figure 6.

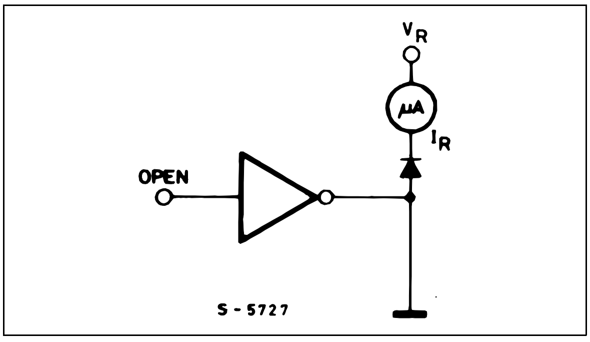


Figure 7.

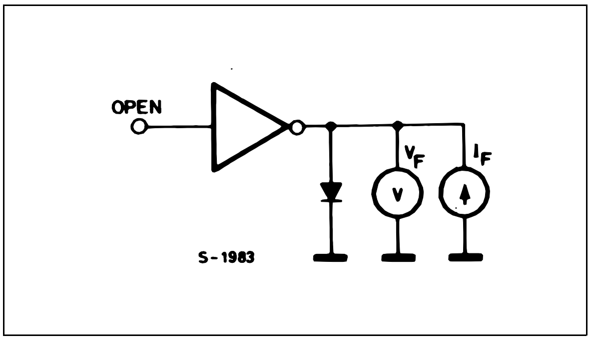


Figure 8: Collector Current versus Input Current

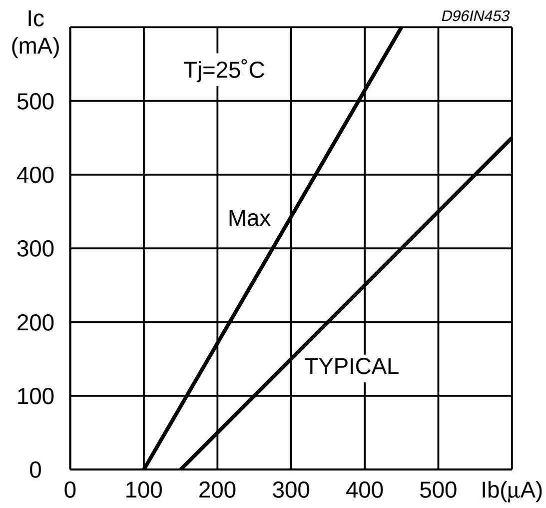


Figure 9: Collector Current versus Saturation Voltage

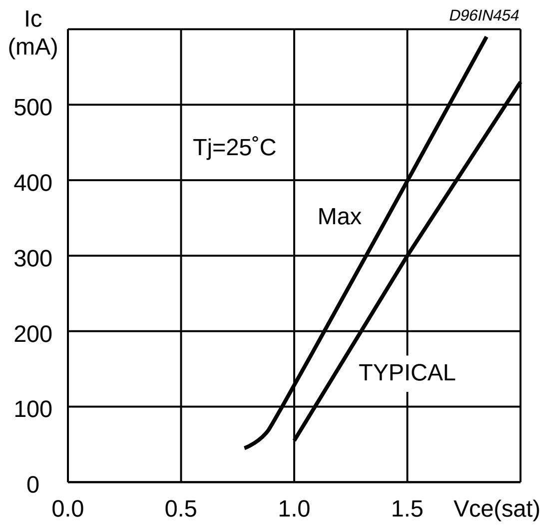


Figure 10: Peak Collector Current versus Duty Cycle

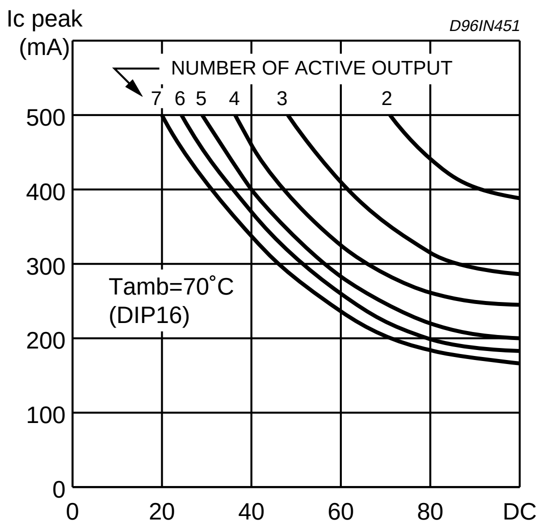
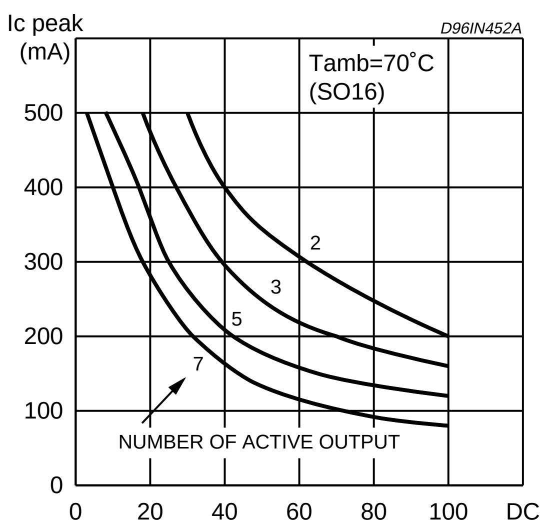
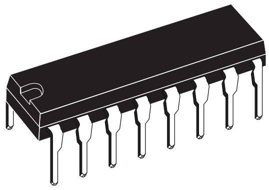


Figure 11: Peak Collector Current versus Duty Cycle

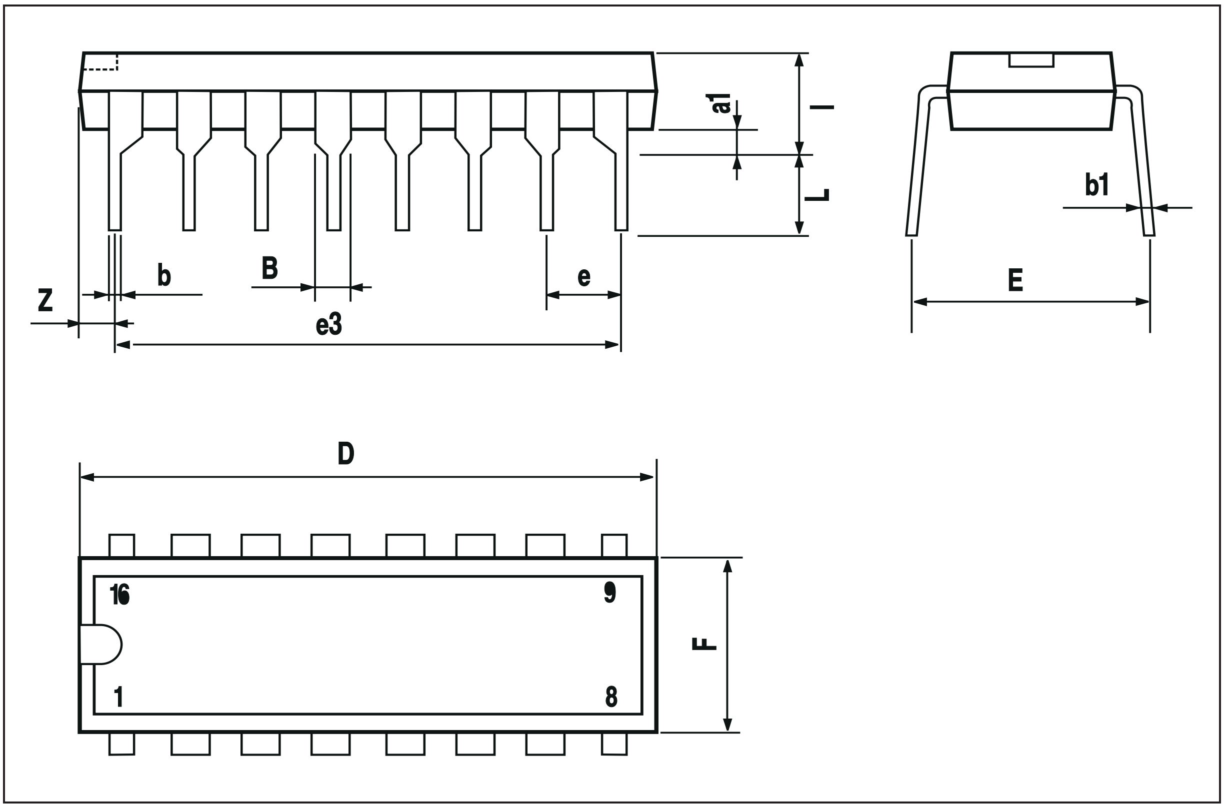


DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
a1	0.51			0.020		
B	0.77		1.65	0.030		0.065
b		0.5			0.020	
b1		0.25			0.010	
D			20			0.787
E		8.5			0.335	
e		2.54			0.100	
e3		17.78			0.700	
F			7.1			0.280
I			5.1			0.201
L		3.3			0.130	
Z			1.27			0.050

OUTLINE AND MECHANICAL DATA

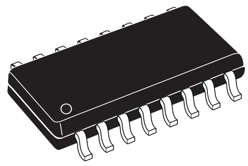


DIP16



DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			1.75			0.069
a1	0.1		0.25	0.004		0.009
a2			1.6			0.063
b	0.35		0.46	0.014		0.018
b1	0.19		0.25	0.007		0.010
C		0.5			0.020	
c1	45° (typ.)					
D (1)	9.8		10	0.386		0.394
E	5.8		6.2	0.228		0.244
e		1.27			0.050	
e3		8.89			0.350	
F (1)	3.8		4	0.150		0.157
G	4.6		5.3	0.181		0.209
L	0.4		1.27	0.016		0.050
M			0.62			0.024
S	8°(max.)					

OUTLINE AND MECHANICAL DATA



SO16 Narrow

(1) D and F do not include mold flash or protrusions. Mold flash or potrusions shall not exceed 0.15mm (.006inch).